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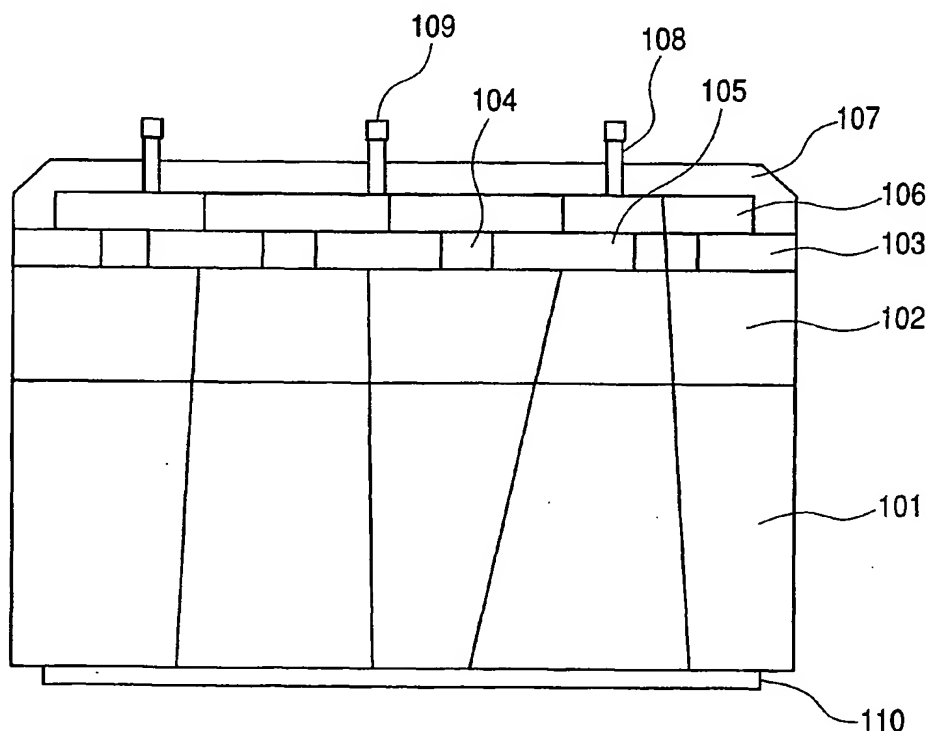
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(54) Title: SOLAR CELL



(57) Abstract: Provided is a solar cell having a silicon substrate for a solar cell, the substrate being formed by allowing a high-purity polycrystalline silicon layer to grow on a surface of a base that is sliced from a polycrystalline silicon ingot which is obtained by melting metal-grade silicon and solidifying the silicon in one direction, wherein a layer having a non-doped amorphous silicon phase and a microcrystalline silicon phase mixed together is stacked on the high-purity polycrystalline silicon layer.

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